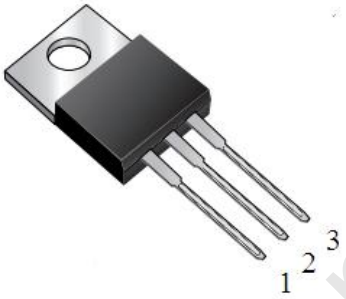
FEATURE

- 20A,60V,RDS(ON)=36mΩ@VGS
- =10V/10A Low gate charge
- Low Ciss
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



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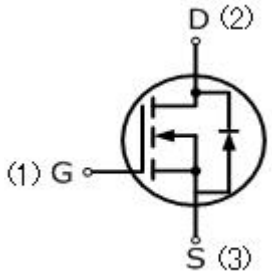


Absolute Maximum Ratings(T_C=25℃,unless otherwise noted)

Parameter		Symbol	IRFZ44N-A	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	
Continuous Drain Current		I_D	20	A
Pulsed Drain Current(Note1)		I_{DM}	80	
Single Pulse Avalanche Energy (Note 2)		E_{AS}	155	mJ
Avalanche Current(Note1)		I_{AR}	20	A
Repetitive Avalanche Energy (Note1)		E_{AR}	5.3	mJ
Reverse Diode dV/dt (Note 3)		dv/dt	7.0	V/ns
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55 to +150	℃
Maximum lead temperature for soldering purposes, 1/8″from case for 5 seconds		T_L	260	℃
Mounting Torque	6-32 or M3 screw		10	lbf • in
			1.1	N • m

Electrical Characteristics (T_c=25℃,unless otherwise noted)

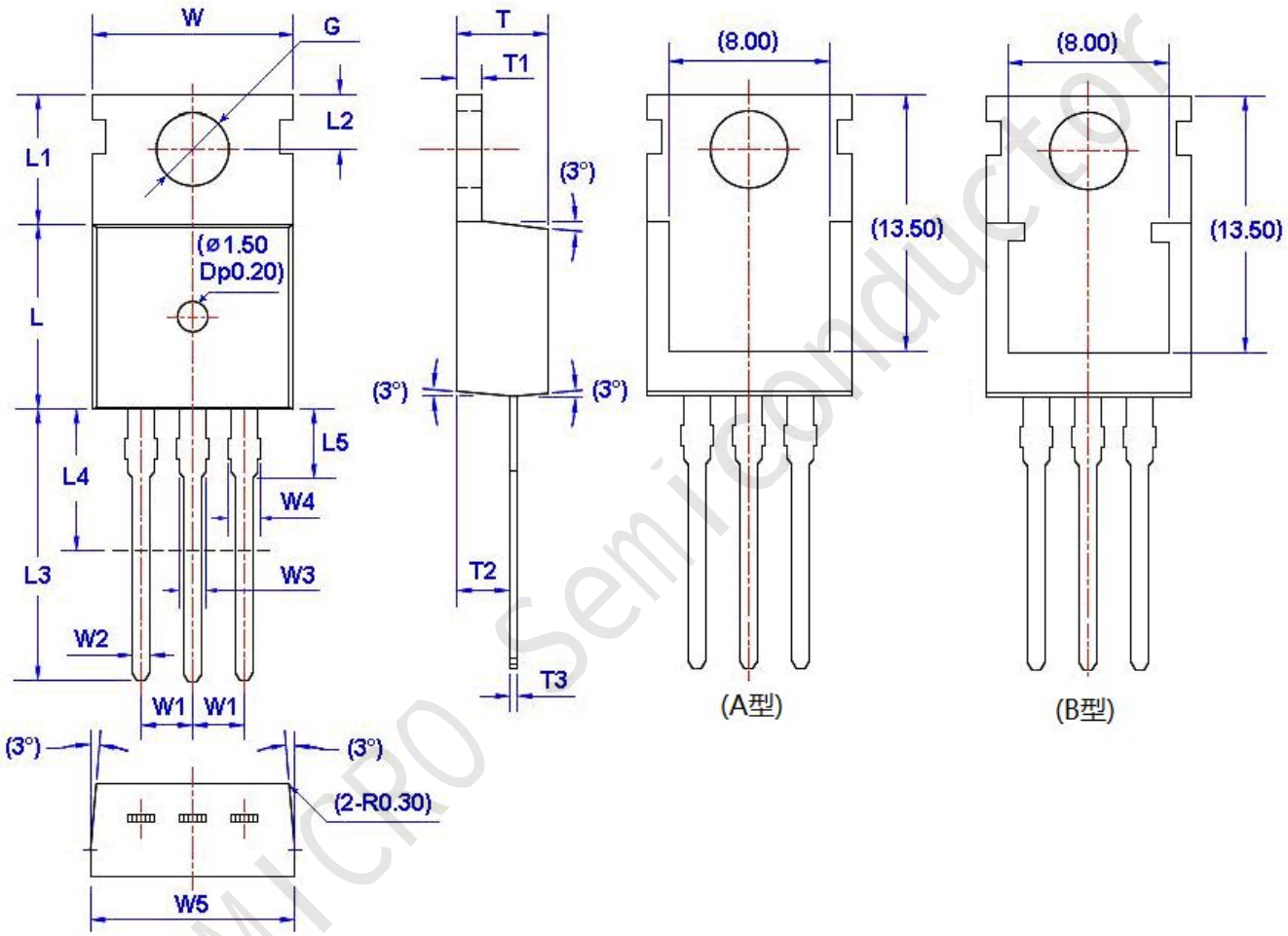
Parameter	Symbol	Test Conditions	Mix	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=250uA	60	—	—	V
Breakdown Temperature Coefficient	ΔBV_{DSS} /ΔT_J	Reference to 25℃, I_D=250uA	—	0.5	—	V/℃
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V,V_{GS}=0V	—	—	1	uA
Gate-Body Leakage Current,Forward	I_{GSSF}	V_{GS}=20V,V_{DS}=0V	—	—	100	nA
Gate-Body Leakage Current,Reverse	I_{GSSR}	V_{GS}=-20V,V_{DS}=0V	—	—	-100	nA
On Characteristics						
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS}=10V,I_D=250uA	1.0	—	3.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=10A	—	—	36	mΩ
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=25V,V_{GS}=0V, f=1.0MHZ	—	450	590	pF
Output Capacitance	C_{oss}		—	170	220	pF
Reverse Transfer Capacitance	C_{rss}		—	25	35	pF
Switching Characteristics						
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=30V,I_D=10A, R_G=25Ω (Note4,5)	—	5	20	ns
Turn-On Rise Time	t_r		—	45	100	ns
Turn-Off Delay Time	$t_{d(off)}$		—	20	50	ns
Turn-Off Fall Time	t_f		—	25	60	ns
Total Gate Charge	Qg	V_{DS}=48V,I_D=20A, V_{GS}=10V, (Note4,5)	—	11.5	15	nC
Gate-Source Charge	Qgs		—	3	—	nC
Gate-Drain Charge	Qgd		—	4.5	—	nC
Drain-Source Body Diode Charcteristics and Maximum Ratings						
Continuous Diode Forward Current	I_S		—	—	20	A
Pulsed Diode Forward Current	I_{SM}		—	—	80	A
Diode Forward Voltage	V_{SD}	I_S=20A,V_{GS}=0V	—	—	1.5	V
Reverse Recovery Time	t_{rr}	V_{GS}=0V,I_S=20A, dI_F/dt=100A/us, (Note4)	—	43	—	ns
Reverse Recovery Charge	Q_{rr}		—	50	—	uC

Notes

1. Repetitive Rating:pulse width limited by maximum junction temperature.
2. V_{DD}=10V,L=1mH,R_g=25Ω,I_{AS}=20A , T_J=25℃.
3. I_{SD}≤I_D,dI/dt=200A/us,V_{DD}≤BV_{DSS},starting T_J=25℃.
4. Pulse width≤300us;duty cycle≤2%.
5. Repetitive rating; pulse width limited by maximum junction temperature.

TO-220AB

Unit: mm



Symbol	Size		Symbol	Size		Symbol	Size		Symbol	Size	
	Min	Max		Min	Max		Min	Max		Min	Max
W	9.66	10.28	W5	9.80	10.20	L4**	6.20	6.60	T3	0.45	0.60
W1	2.54（TYP）		L	9.00	9.40	L5	2.79	3.30	G(Φ)	3.50	3.70
W2	0.70	0.95	L1	6.40	6.80	T	4.30	4.70			
W3	1.17	1.37	L2	2.70	2.90	T1	1.15	1.40			
W4*	1.32	1.72	L3	12.70	14.27	T2	2.20	2.60			